

Dual 4-Input NAND Gate IC in bare die form

Rev 1.0 7/5/2019

Description

The 74HC20 Dual 4-Input NAND Gate is made using a 2.5µm 5V CMOS process & combines the high speed of LSTTL with CMOS low power consumption. The device performs Boolean functions Y = (A \cdot B \cdot C \cdot D) or Y = \overline{A} + \overline{B} + \overline{C} + \overline{D} in positive logic. Inputs accept standard CMOS outputs or LSTTL outputs using pull-up resistors. Internal circuitry comprises 3 stages & includes buffered output for high noise immunity & stability. Inputs are equipped with protection circuits against static discharge & transient excess voltage.

Ordering Information

The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product places see

54HC20

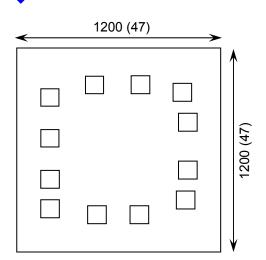
Supply Formats:

- Defaut Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

- High Speed: t_{PD} = 11ns @ 6V (Typ.)
- Low Input Current: 1µA
- Output Drive Capability: 10 loads
- Operating Voltage Range: 2 to 6V
- CMOS High Noise Impunity
- Function compatible with 74LS20.

Die Qin ensions in µm (mils)



Mechanical Specification

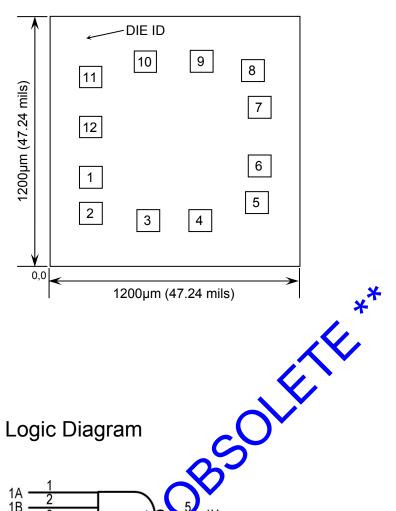
| Die Size (Unsawn) | 1200 x 1200 47 x 47 | μm mils | |
|------------------------|----------------------------|------------|--|
| Minimum Bond Pad Size | 106 x 106 4 x 4 | μm mils | |
| Die Thickness | 350 (±20) 13.78 (±0.79) | μm mils | |
| Top Metal Composition | Al 1%Si 1.1μm | | |
| Back Metal Composition | N/A – Bare S | Si | |





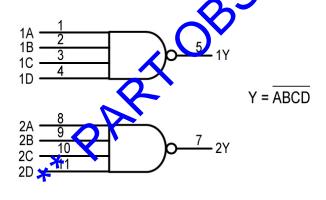
Rev 1.0 7/5/2019

Pad Layout and Functions



| PAD | FUNCTION | COORDIN | 41 55 (mm) |
|-----|-----------------|-------------------------|-------------------|
| ואט | 1011011011 | Х | Υ |
| 1 | 1A | 0.151 | 0.364 |
| 2 | 1B | 0.151 | 0.184 |
| 3 | 1C | 0.427 | 0.151 |
| 4 | 1 | 0.671 | 0.151 |
| 5 | 11 | 0.933 | 0.238 |
| 6 | GND | 0.943 | 0.418 |
| C | 2Y | 0.943 | 0.706 |
| 2 | 2A | 0.909 | 0.886 |
| 9 | 2B | 0.672 | 0.929 |
| 10 | 2C | 0.405 | 0.917 |
| 11 | 2D | 0.151 | 0.853 |
| 12 | V _{CC} | 0.151 | 0.608 |
| CON | NECT CHIP BA | CK TO V _{CC} C | R FLOAT |

Logic Diagram



Pad 12 = V_{CC} Pad 6 = GND

Function Table

| | OUTPUT | | | |
|---|--------|---|---|---|
| Α | В | С | D | Y |
| L | X | X | X | Н |
| X | L | X | X | H |
| X | X | L | X | Н |
| X | X | X | L | Н |
| Н | Н | Н | Н | L |

H = High level (steady state) L = Low level (steady state) X = don't care





Rev 1.0 7/5/2019

Absolute Maximum Ratings¹

| PARAMETER | SYMBOL | VALUE | UNIT |
|--|------------------|------------------------------|------|
| Supply Voltage (Referenced to GND) | V _{CC} | -0.5 to +7.0 | V V |
| DC Input Voltage (Referenced to GND) | V _{IN} | -1.5 to V _{CC} +1.5 | |
| DC Output Voltage (Referenced to GND) | V _{OUT} | -0.5 to V _{CC} +0.5 | V |
| DC Input Current, per pad | I _{IN} | ±20 | mA |
| DC Output Current, per pad | l _{out} | ±25 | mA |
| DC Supply Current, V _{CC} or GND, per pad | I _{CC} | ±50 | mA |
| Power Dissipation in Still Air ² | P _D | 750 | mW |
| Storage Temperature Range | T _{STG} | -65 10 15 | °C |

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die acceptance and assembly method.

Recommended Operating Conditions³ (Voltages referenced to GND)

| | 4 | | | |
|-----------------------------|-----------------------------------|------------|-----------------|-------|
| PARAMETER | SYMBOL | MIN | MAX | UNITS |
| Supply Voltage | V _{CC} | 7 2 | 6 | V |
| DC Input or Output Voltage | V _{IN} ,V _{OUT} | 0 | V _{CC} | V |
| Operating Temperature Range | T _J | -40 | +85 | °C |
| | V _C /= 2.0 | 0 | 1000 | |
| Input Rise or Fall Times | $t_r, t_f V_{CC} = 4.5V$ | 0 | 500 | ns |
| | V _{ec} = 6V | 0 | 400 | |

^{3.} This device contains protection circuitry to guar against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range $GND \le (V_{IN} \text{ or } V_{OU}) \le V_{C}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC Electrical Characteristics (Voltages referenced to GND)

| PARAMETER | SYMBOL | DL V _{cc} CONDITIONS | CONDITIONS | LIMITS | | | UNITS |
|---------------------------------|-----------------|-------------------------------|--------------------------|--------|-------------|-------|-------|
| | STWIDOL | | 25°C | 85°C | FULL RANGE⁴ | ONITO | |
| Minimum High-Level | | 2V | $V_{OUT} = 0.1V$ or | 1.5 | 1.5 | 1.5 | |
| | V _{IH} | 4.5V V _{CC} -0.1V | 3.15 | 3.15 | 3.15 | V | |
| | | 6.0V | I _{OUT} ≤ 20μA | 4.2 | 4.2 | 4.2 | |
| Maximum Low-Level Input Voltage | | 2V | $V_{OUT} = 0.1V$ or | 0.3 | 0.3 | 0.3 | |
| | V_{IL} | 4.5V | V _{CC} -0.1V | 0.9 | 0.9 | 0.9 | V |
| | 6.0V | / I _{OUT} ≤ 20μA | 1.2 | 1.2 | 1.2 | | |

^{4.} -40° C $\leq T_{J} \leq +85^{\circ}$ C





Rev 1.0 7/5/2019

DC Electrical Characteristics Continued (Voltages referenced to GND)

| PARAMETER | SYMBOL | OL V _{CC} CONDITIO | | LIMITS | | | UNITS |
|-------------------------------------|-----------------|-----------------------------|--|--------|-------------|------------|-------|
| TANAMETER | OT MIDGE | ▼ CC | CONDITIONS | 25°C | 85°C | FULL RANGE | |
| | | 2V | \/ =\/ or\/ | 1.9 | 1.9 | 1.9 | |
| | | 4.5V | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu \text{A}$ | 4.4 | 4.4 | 4.4 | V |
| Minimum High-Level | | 6.0V | 1.0011 = 2012. | 5.9 | 5.9 | 5.9 | |
| Output Voltage | V _{OH} | 4.5V | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 4.0 \text{mA}$ | 3.98 | 3.84 | 3.84 | V |
| | | 6.0V | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 5.2 \text{mA}$ | 5.48 | 5/54 | 5.34 | V |
| | V _{OL} | 2V | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$ | 0.1 | 0.1 | 0.1 | V |
| | | 4.5V | | 0.1 | 9 .1 | 0.1 | |
| Maximum Low-Level | | 6.0V | | 0.1 | 0.1 | 0.1 | |
| Output Voltage | | 4.5V | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 4.0 \text{mA}$ | 0.26 | 0.33 | 0.33 | V |
| | | 6.0V | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 5.2 \text{ in } A$ | 0.26 | 0.33 | 0.33 | V |
| Maximum Input Leakage Current | I _{IN} | 6.0V | V _{IN} ⇒ V _{CC} or GMD | ±0.1 | ±1.0 | ±1.0 | μА |
| Maximum Quiescent Supply Current | I _{cc} | 6.0V | $V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0\mu A$ | 2 | 20 | 20 | μA |

AC Electrical Characteristics⁵

| PARAMETER | SYM:OL V _{cc} | Vac | CONDITIONS | LIMITS | | | UNITS | | |
|-----------------------------------|-------------------------------------|------------|---------------------------------------|--------|------------------------|-------|-------|----|----|
| | | CONDITIONS | 25°C | 85°C | FULL RANGE⁴ | ONITO | | | |
| Maximum Propagation | | 2V | 0 - 50-5 | 90 | 115 | 115 | | | |
| Delay, Input A, B, C, D | t _{PLH} , t _{PHL} | 4.5V | $C_L = 50pF,$ $t_c = t_f = 6ns$ | 18 | 23 | 23 | ns | | |
| to Output Y | | 6.0V | 4 4 5115 | 15 | 20 | 20 | | | |
| Maximum Output Rise | 2 | 2V | 0 - 50-5 | 75 | 95 | 95 | | | |
| and Fall I me Any | t _{TLH,} t _{THL} | 4.5V | $C_L = 50pF,$ $t_r = t_f = 6ns$ | 15 | 19 | 19 | ns | | |
| Outout | | 6.0V | | 13 | 16 | 16 | | | |
| Maximum Input Capacitance | C _{IN} | - | - | 10 | 10 | 10 | pF | | |
| Power Dissipation | C _{PD} - | | · · · · · · · · · · · · · · · · · · · | | T _J = 25°C, | | TYPIC | AL | pF |
| Capacitance Per Gate ⁶ | | | V _{CC} =5.0V | | 26 | | Pi | | |

^{5.} Not production tested in die form, characterized by chip design and tested in package.

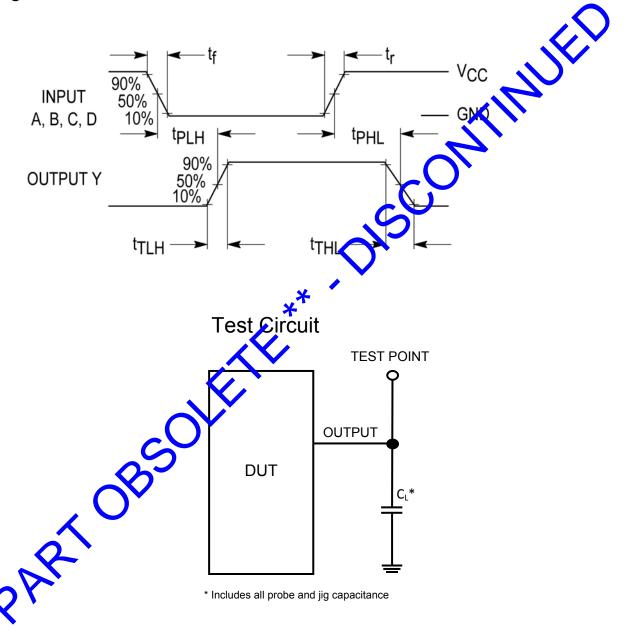


^{6.} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.



Rev 1.0 7/5/2019

Switching Waveform



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